

REMARKS

This application has been carefully reviewed in light of the Office Action dated July 27, 2007. Claims 1, 2, and 4 to 6 are in the application, with Claim 1 being independent. Claims 3 and 7 have been cancelled without prejudice. Claims 1 and 6 have been amended herein. Reconsideration and further examination are respectfully requested.

Claim 1 was objected to for an alleged informality. This matter has been attended to by the amendments made to Claim 1.

Claims 1 to 5 were rejected under 35 U.S.C. § 102(b) over U.S. Patent No. 5,977,477 (Shiozaki). Claim 6 was rejected under 35 U.S.C. § 102(b) over Shiozaki in view of IEEE Transactions on Electronic Devices, vol. ED-24, No. 4, April 1977 (Wronski). Claim 7 was rejected under 35 U.S.C. § 103(a) over Shiozaki in view of Thin Solid Films, vol. 354, 1999, pp. 227-231 (Baik). These rejections are respectfully traversed.

According to a feature of the invention as recited by Claim 1, the adsorption preventive layer comprises a non-single crystal silicon material in which an amount of dopant is decreased compared to the p- or n-type semiconductor layer provided adjacent to the zinc oxide layer.

None of Shiozaki, Wronski, and Baik, even in the proposed combinations, assuming, *arguendo*, that such could be combined, is seen to disclose or suggest at least the above-discussed feature.

The dependent claims are also submitted to be patentable because they set forth additional aspects of the present invention and are dependent from the independent claim discussed above. Therefore, separate and individual consideration of each dependent claim is respectfully requested.

The application is believed to be in condition for allowance, and a Notice of Allowance is respectfully requested.

No fees are believed due; however, should it be determined that additional fees are required, the Director is hereby authorized to charge such fees and any additional fees under 37 C.F.R. §§ 1.16 and 1.17 which may be required during the entire pendency of this application, or to credit any overpayment, to Deposit Account 50-3939.

Applicants' undersigned attorney may be reached in our Costa Mesa, California office by telephone at (714) 540-8700. All correspondence should be directed to our address given below.

Respectfully submitted,

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